



#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	Package	I <sub>D max</sub> T <sub>A</sub> = +25°C
60)/	$38m\Omega @ V_{GS} = 10V$	U-DFN2020-6	6.5A
60V	$47m\Omega @ V_{GS} = 4.5V$	Type E	5.2A

#### Description

This new generation MOSFET has been designed to minimize the onstate resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- General Purpose Interfacing Switch
- Power Management Functions

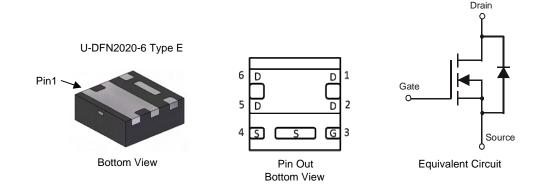
#### **60V N-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Features and Benefits**

- 100% Unclamped Inductive Switch (UIS) test in production
- 0.6mm profile ideal for low profile applications
- PCB footprint of 4mm<sup>2</sup>
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: U-DFN2020-6 Type E
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.0065 grams (approximate)



#### Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Quantity per reel
DMN6040SFDE-7	N8	7	3,000
DMN6040SFDE-13	N8	13	10,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and</li>

<1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com.

## **Marking Information**



 $\begin{array}{l} \mathsf{N8} = \mathsf{Product} \ \mathsf{Type} \ \mathsf{Marking} \ \mathsf{Code} \\ \mathsf{YM} = \mathsf{Date} \ \mathsf{Code} \ \mathsf{Marking} \\ \mathsf{Y} = \mathsf{Year} \ (\mathsf{ex:} \ \mathsf{Y} = \mathsf{2011}) \\ \mathsf{M} = \mathsf{Month} \ (\mathsf{ex:} \ 9 = \mathsf{September}) \end{array}$ 

Date	Code	Key
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Date Code hoy												
Year	201	1	2012		2013	20	14	2015		2016	2	2017
Code	Y		Z		А	I	3	С		D		E
-			1		1			*		-		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage		V <sub>DSS</sub>	60	V	
Gate-Source Voltage		V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note C) // 10//	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	5.3 4.1	A
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	t<10s	t<10s $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		6.5 5.1	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)		I <sub>DM</sub>	30	A	
Maximum Body Diode Continuous Current		Is	2.5	A	
Avalanche Current (Note 7) L = 0.1mH	I <sub>AR</sub>	14.2	A		
Avalanche Energy (Note 7) L = 0.1mH	E <sub>AR</sub>	10	mJ		

## **Thermal Characteristics**

Characteristic		Symbol	Value	Units	
Total Dower Dissinction (Note 5)	T <sub>A</sub> = +25°C	Р	0.66	W	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +70°C	PD	0.42	vv	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	Р	189	°C/W	
	t<10s	t<10s R <sub>0JA</sub>	132	C/W	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	Π_	2.03	W	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +70°C	PD	1.31	vv	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	D	61	°C/W	
Thermal Resistance, Junction to Amplent (Note 6)	t<10s	$R_{ heta JA}$	43		
Thermal Resistance, Junction to Case (Note 6)		$R_{ ext{ heta}JC}$	9.3		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	С°	

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

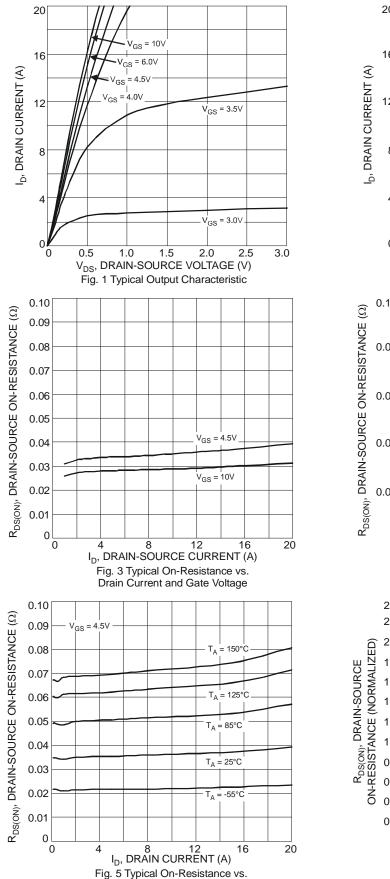
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	<b>BV</b> <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	100	nA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance		_	30	38		V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.3A
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	_	35	47	mΩ	$V_{GS} = 4.5V, I_D = 4A$
Forward Transfer Admittance	Y <sub>fs</sub>	_	4.5	_	S	$V_{DS} = 10V, I_D = 4.3A$
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1A$
DYNAMIC CHARACTERISTICS (Note 9)			÷			
Input Capacitance	C <sub>iss</sub>	_	1287	_		
Output Capacitance	C <sub>oss</sub>	_	57	_	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	44	_		T = T.000172
Gate Resistance	R <sub>G</sub>	_	1.2		Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	22.4	_		
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	10.4	_	nC	$V_{DS} = 30V.$ In = 4.3A
Gate-Source Charge	Q <sub>gs</sub>	_	4.9	_	nc	$v_{DS} = 30v, I_D = 4.3A$
Gate-Drain Charge	Q <sub>gd</sub>	_	3.0	_		
Turn-On Delay Time	t <sub>D(on)</sub>	_	6.6	_		
Turn-On Rise Time	tr	_	8.1	_	nS	$V_{GS} = 10V, V_{DD} = 30V, R_G = 6\Omega,$
Turn-Off Delay Time	t <sub>D(off)</sub>	_	20.1	_	15	I <sub>D</sub> = 4.3A
Turn-Off Fall Time	t <sub>f</sub>	_	4.0	_		
Body Diode Reverse Recovery Time	t <sub>rr</sub>		18		nS	I <sub>S</sub> = 4.3A, dI/dt = 100A/µs
Body Diode Reverse Recovery Charge	Qrr		11.9	_	nC	I <sub>S</sub> = 4.3A, dl/dt = 100A/µs

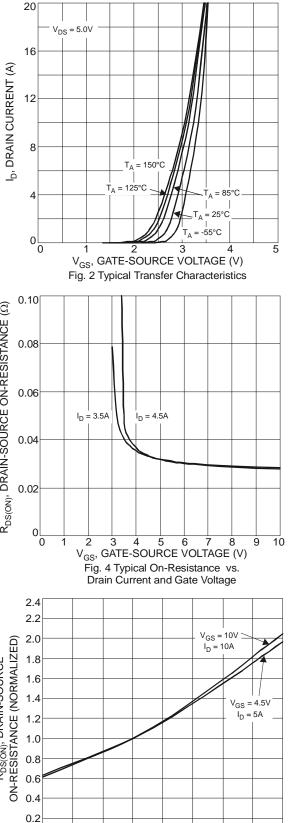
 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

7.  $I_{AR}$  and  $E_{AR}$  rating are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ .

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.







50 TJ, JUNCTION TEMPERATURE (°C) Fig. 6 On-Resistance Variation with Temperature

75

100

125

25

Drain Current and Temperature

0

-50

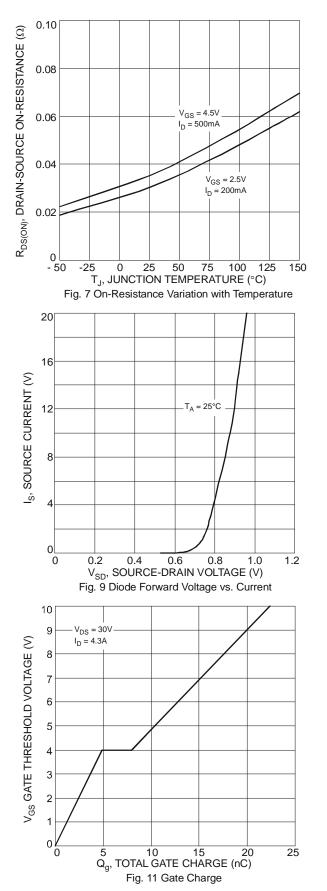
-25

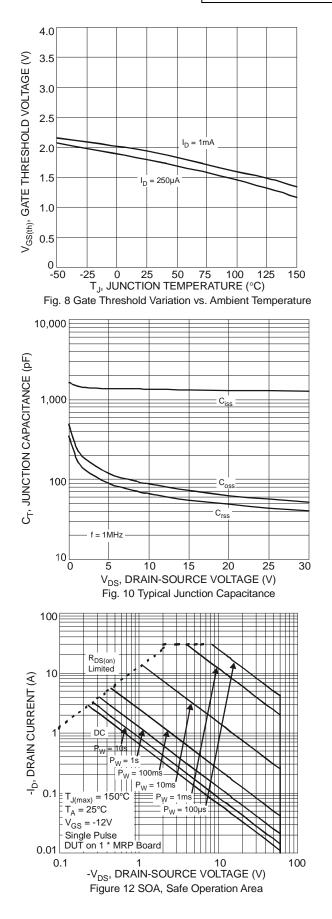
0

150

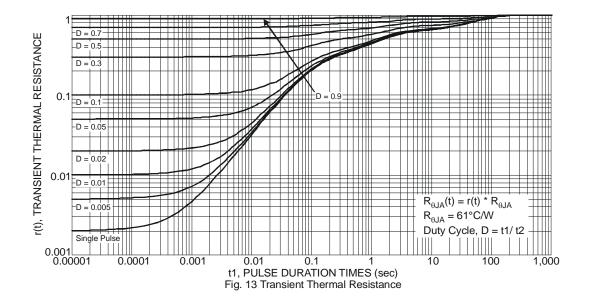






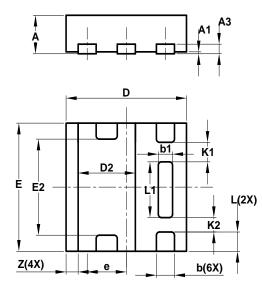






## **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

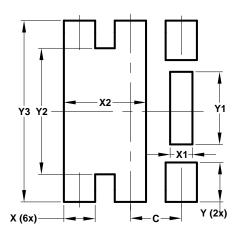


U-DFN2020-6								
Туре Е								
Dim	Dim Min Max Typ							
Α	0.57	0.63	0.60					
A1	0	0.05	0.03					
A3			0.15					
b	0.25	0.35	0.30					
b1	0.185	0.285	0.235					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
E	1.95	2.05	2.00					
E2	1.40	1.60	1.50					
е	-	—	0.65					
L	0.25	0.35	0.30					
L1	0.82	0.92	0.87					
K1		_	0.305					
K2		_	0.225					
Z		_	0.20					
All	Dimens	ions in r	nm					



#### Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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